

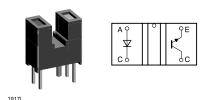
Transmissive Optical Sensor with Phototransistor Output

Description

The TCST1030 and TCST1030L are transmissive sensors that include an infrared emitter and phototransistor, located face-to-face on the optical axes in a leaded package which blocks visible light. TCST1030L is the long lead version.

Features

- Package type: Leaded
- Detector type: Phototransistor
- Dimensions:
- L 8.3 mm x W 4.7 mm x H 8.15 mm
- Gap: 3 mm
- Aperture: none
- Typical output current under test: I_C = 2.4 mA
- Daylight blocking filter
- Emitter wavelength 950 nm
- Lead (Pb)-free soldering released
- Lead (Pb)-free component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



Applications

- Optical switch
- Shaft encoder
- Detection of opaque material such as paper
- Detection of magnetic tapes

Order Instructions

Part Number	Remarks	Minimum Order Quantity
TCST1030	3.4 mm lead length	5200 pcs, 65 pcs/tube
TCST1030L	16 mm lead length	2600 pcs, 65 pcs/tube

Absolute Maximum Ratings

 T_{amb} = 25 °C, unless otherwise specified

Coupler

Parameter	Test condition	Symbol	Value	Unit
Total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	P _{tot}	250	mW
Operation temperature range		T _{amb}	- 25 to + 85	°C
Storage temperature range		T _{stg}	- 25 to + 100	°C
Soldering temperature	1.6 mm from case, $t \leq 10 \mbox{ s}$	T _{sd}	260	°C

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Input (Emitter)

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V _R	6	V
Forward current		١ _F	60	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	3	A
Power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	P _V	100	mW
Junction temperature		Tj	100	°C

Output (Detector)

Parameter	Test condition	Symbol	Value	Unit
Collector emitter voltage		V _{CEO}	70	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		Ι _C	100	mA
Power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	P _V	150	mW
Junction temperature		Тj	100	°C

Electrical Characteristics

 T_{amb} = 25 °C, unless otherwise specified

Coupler

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Collector current	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$	۱ _C	1.2	2.4		mA
Collector emitter saturation voltage	I _F = 10 mA, I _C = 1 mA	V _{CEsat}			0.8	V

Input (Emitter)

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Forward voltage	I _F = 60 mA	V _F		1.25	1.5	V
Junction capacitance	V _R = 0, f = 1 MHz	Cj		50		pF

Output (Detector)

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Collector emitter voltage	I _C = 1 mA	V _{CEO}	70			V
Emitter collector voltage	I _E = 10 μA	V _{ECO}	7			V
Collector dark current	$V_{CE} = 25 \text{ V}, \text{ I}_{F} = 0, \text{ E} = 0$	I _{CEO}		10	100	nA

Switching Characteristics

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Turn-on time	$I_C = 1 \text{ mA}, V_{CE} = 5 \text{ V},$ $R_L = 100 \Omega \text{ (see figure 1)}$	t _{on}		15.0		μs
Turn-off time	$I_{C} = 1 \text{ mA}, V_{CE} = 5 \text{ V},$ $R_{L} = 100 \Omega \text{ (see figure 1)}$	f _{off}		10.0		μs



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+ 5 V 0 I_C = 1 mA; adjusted by I_F $R_{G} = 50 \ \Omega$ $\frac{t_p}{T} = 0.01$ \mathbb{V} t_p = 50 μs 0 Channel I Oscilloscope -0 Channel II $R_L \geq ~1~M\Omega$ $C_L \le 20 \text{ pF}$ 50 Ω $100\,\Omega$ 20223

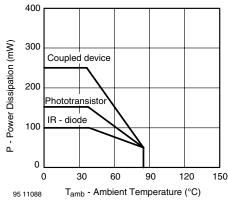
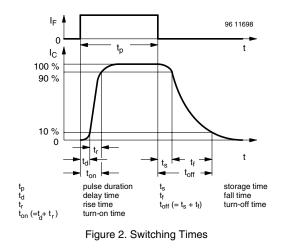


Figure 1. Test Circuit for ton and toff



Typical Characteristics

 $T_{amb} = 25$ °C, unless otherwise specified

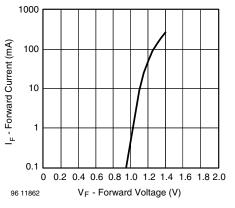
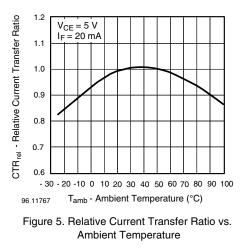


Figure 4. Forward Current vs. Forward Voltage

Figure 3. Power Dissipation Limit vs. Ambient Temperature



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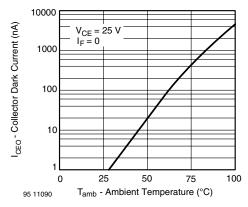


Figure 6. Collector Dark Current vs. Ambient Temperature

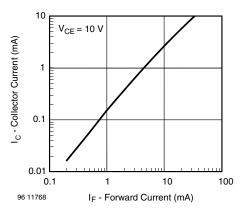


Figure 7. Collector Current vs. Forward Current

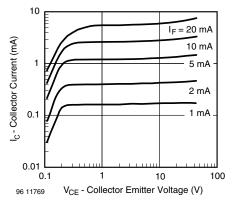


Figure 8. Collector Current vs. Collector Emitter Voltage

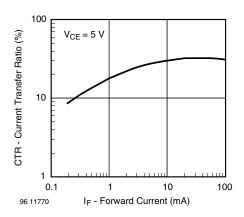


Figure 9. Current Transfer Ratio vs. Forward Current

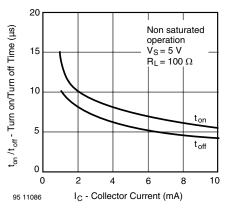


Figure 10. Turn on/off Time vs. Collector Current

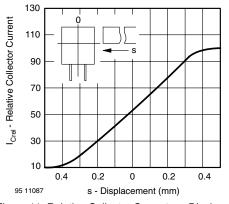
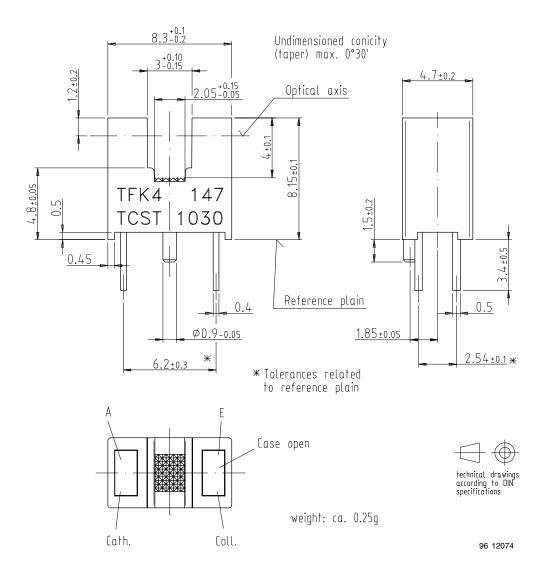


Figure 11. Relative Collector Current vs. Displacement



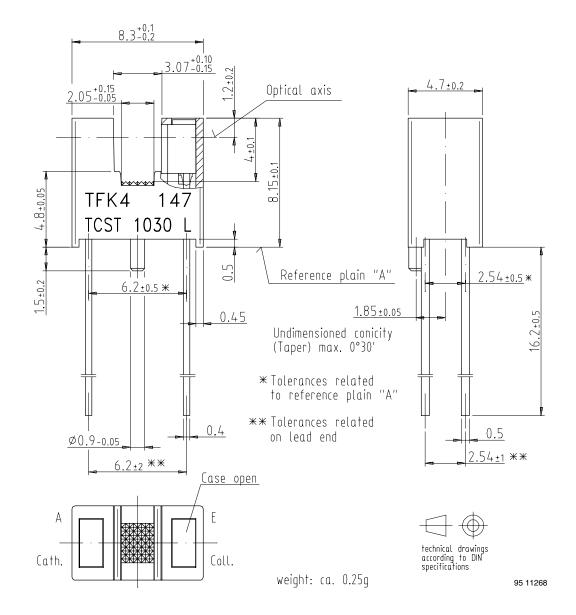


Package Dimensions in mm



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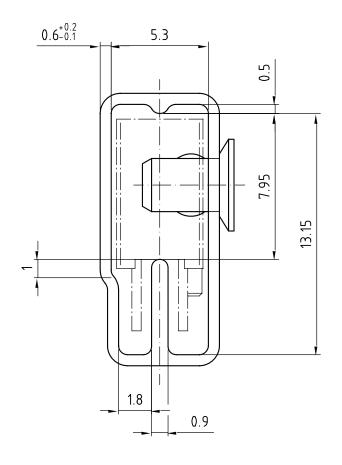






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Tube Dimensions in mm



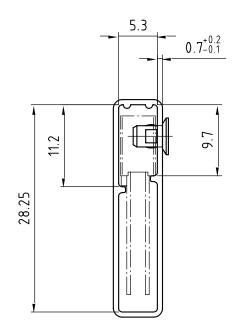
With stopper pins Tolerance: ±0.5mm Length: 575±1mm

All dimensions in mm

Drawing-No.: 9.700-5140.01-4 Issue: 1; 25.02.00 20253

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With stopper pins Tolerance: ±0.5mm Length: 575±1mm All dimensions in mm

Drawing-No.: 9.700-5205.01-4 Issue: 1; 25.02.00 20254



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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

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